

ABSTRACT

MANUFACTURING METHOD FOR SEMICONDUCTOR DEVICE AND BONDED
WAFER

The present disclosure has an object to enhance productivity and reduce
5 cracking in a wafer in manufacture of a semiconductor device reusing the wafer. A
manufacturing method for a semiconductor device according to the present disclosure
includes the steps of: (a) dividing each of a plurality of SiC wafers (13, 17) in a thickness
direction to thereby obtain at least one divided wafer (20, 23) not including a device
structure (12, 16) from each of the SiC wafers (13, 17); (b) bonding a plurality of the
10 divided wafers (20, 23) obtained from different SiC wafers (13, 17) to obtain a bonded
wafer (24); and (c) forming the device structure (26) on a front surface of the bonded
wafer (24).

Fig. 1